Si3865BDV vs. Si3865DV

Description: Load Switch with Level-Shift
Package: TSOP-6
Pin Out: Identical

Part Number Replacements:
Si3865BDV-T1 Replaces Si3865DV-T1
Si3865BDV-T1-E3 (Lead (Pb)-free version) Replaces Si3865DV-T1-E3 (Lead (Pb)-free version)

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted					
Parameter		**Symbol**	**Si3865BDV**	**Si3865DV**	**Unit**
Input Voltage		V_{IN}	8	8	V
ON/OFF Voltage		$V_{ON/OFF}$	± 8	± 8	
Load Current	Continuous	I_L	2.9	2.7	A
	Pulsed		6	6	
Continuous Intrinsic Diode Conduction		I_S	- 1	- 1	
Power Dissipation		P_D	0.83	0.83	W
Operating Junction and Storage Temperature Range		T_j and T_{stg}	- 55 to 150	- 55 to 150	°C
Maximum Junction-to-Ambient		R_{thJA}	150	150	°C/W

SPECIFICATIONS T_J = 25 °C, unless otherwise noted									
Parameter		**Symbol**	**Si3865BDV**			**Si3865DV**			**Unit**
			Min	**Typ**	**Max**	**Min**	**Typ**	**Max**	
OFF Characteristic									
Reverse Leakage Current		I_{FL}			1			1	µA
Diode Forward Voltage		V_{SD}		- 0.77	- 1		- 0.7	- 1	V
ON Characteristic									
Input Voltage Range		V_{IN}	1.8		8	1.8		8	nC
On-Resistance (P-Channel) at 1 A	V_{GS} = 4.5 V	$r_{DS(on)}$		0.045	0.060		0.064	0.080	Ω
	V_{GS} = 2.5 V			0.075	0.100		0.092	0.110	
	V_{GS} = 1.8 V			0.135	0.175		0.135	0.175	
On-State Drain Current (P-Channel)	V_{IN} = 5 V	$I_{D(on)}$	1			1			A
	V_{IN} = 13 V		1			1			

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.